

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	IS&R	L1	2	("5798137").PN.	US- PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/2 9 18:16	
2	BRS	L2	1573	silicon ADJ hydride and (coating or coatings or layer or layers) and substrate	US- PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/2 9 18:18	
3	BRS	L3	4	2 and hydrogen ADJ permeation and passivation	US- PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/2 9 18:20	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	702	2 and silicon WITH (deposited or deposition)	US- PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/2 9 18:23	
5	BRS	L6	2	5 and hydrogen ADJ permeation	US- PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/2 9 18:24	
6	BRS	L5	126	4 and (passivating or passivation)	US- PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/2 9 18:25	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	10	5 and corrosion and vacuum	US-PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/29 18:32	
8	BRS	L8	118	5 and layer WITH silicon	US-PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/29 18:34	
9	BRS	L9	30	8 and (protect or protects or protection) and (corrosion or passivation or passivating or corroding)	US-PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/29 18:55	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	30	2 and silicon ADJ (dusts or dust or particles)	US- PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/2 9 18:55	
11	BRS	L11	23	10 and layer WITH silicon	US- PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/2 9 18:57	
12	BRS	L12	23	11 and silicon ADJ hydride	US- PGPUB ; USPAT ; USOCR ; EPO; JPO; DERWE NT; IBM_T DB	2005/04/2 9 19:20	

	U	1	Document ID	Issue Date	Pages	Title
1			US 20040175579 A1	20040909	7	Method for chemical vapor deposition of silicon on to substrates for use in corrosive and vacuum environments
2			US 20040175578 A1	20040909	6	Method for chemical vapor deposition of silicon on to substrates for use in corrosive and vacuum environments
3			US 20030170280 A1	20030911	25	Dermatological composition
4			US 20030013280 A1	20030116	115	Semiconductor thin film forming method, production methods for semiconductor device and electrooptical device, devices used for these methods, and semiconductor device and electrooptical device

	Current OR	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3
1	428/446			Smith, David A. et al.	X				
2	428/446	428/450; 428/457		Smith, David A. et al.	X				
3	424/401			Canham, Leigh T et al.	X				
4	438/487	117/84; 117/88; 117/89; 118/715; 118/725; 257/E21.133 ; 257/E21.413 ; 257/E21.414 ; 257/E21.416 ; 257/E29.275 ; 257/E29.293 ; 257/E29.294 ; 257/E29.296 ; 257/E29.297 ; 438/486; 438/492; 438/97		Yamanaka, Hideo	X				

	U	1	Document ID	Issue Date	Pages	Title
5			US 6879017 B2	20050412	13	Methods and structures for metal interconnections in integrated circuits
6			US 6780649 B2	20040824	22	Photoluminescent semiconductor materials
7			US 6767775 B1	20040727	20	Method of manufacturing thin-film transistor
8			US 6630356 B1	20031007	22	Photoluminescent semiconductor materials

	Current OR	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3
5	257/508	257/19; 257/503; 257/616; 257/734; 257/741; 257/742; 257/758; 257/761		Ahn; Kie Y. et al.	X				
6	436/172	205/118; 205/122; 205/792; 205/793; 257/1; 257/E33.018 ; 422/82.05; 422/82.08; 422/82.09; 436/72		Armstrong; David W. et al.	X				
7	438/156	257/E21.114 ; 257/E21.174 ; 257/E21.271		Yudasaka; Ichio et al.	X				
8	436/172	205/118; 205/122; 205/123; 205/777.5; 205/792; 205/793; 257/1; 257/E33.018 ; 422/82.05; 422/82.08; 422/82.09; 436/72		Armstrong; David W. et al.	X				

	U	1	Document ID	Issue Date	Pages	Title
9			US 6541859 B1	20030401	14	Methods and structures for silver interconnections in integrated circuits
10			US 6514801 B1	20030204	18	Method for manufacturing thin-film transistor
11			US 6504224 B1	20030107	14	Methods and structures for metal interconnections in integrated circuits

	Current OR	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3
9	257/742	257/522; 257/743; 257/757; 257/E21.297 ; 257/E21.581 ; 257/E21.585 ; 257/E23.162		Forbes; Leonard et al.	X				
10	438/151	257/E21.114 ; 257/E21.273 ; 257/E21.413 ; 438/166		Yudasaka; Ichio et al.	X				
11	257/508	257/19; 257/503; 257/522; 257/734; 257/758; 257/E21.581 ; 257/E21.585 ; 257/E21.591 ; 257/E23.164		Ahn; Kie Y. et al.	X				

	U	1	Document ID	Issue Date	Pages	Title
12		X	US 6444326 B1	20020903	8	Surface modification of solid supports through the thermal decomposition and functionalization of silanes
13			US 6049090 A	20000411	10	Semiconductor particle electroluminescent display
14	X		US 5254369 A	19931019	13	Method of forming a silicon diffusion and/or overlay coating on the surface of a metallic substrate by chemical vapor deposition
15	X		US 5098576 A	19920324	13	Adsorbents for chromatography and adsorption processes
16	X		US 4905072 A	19900227	24	Semiconductor element

	Current OR	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3
12	428/448	427/255.11; 427/255.15; 427/255.18; 427/255.26; 427/255.27; 427/255.7; 427/387; 427/541; 428/428; 428/429; 428/446; 428/447; 428/450		Smith; David AbbottX					
13	257/13	257/17; 257/94; 257/E33.005		Clark, Jr.; Harry R. X					
14	427/248.1	427/255.18; 427/255.21; 427/314; 427/327		Arai; Juichi et al.					
15	210/656	210/198.2; 210/502.1; 210/635		Cabrera; Karin et al.					
16	257/64	257/65; 257/66; 257/E21.219 ; 257/E29.003		Komatsu; Toshiyuki et al.					

	U	1	Document ID	Issue Date	Pages	Title
17	X		US 4719501 A	19880112	22	Semiconductor device having junction formed from two different hydrogenated polycrystalline silicon layers
18	X		US 4717585 A	19880105	23	Process for forming deposited film
19	X		US 4377564 A	19830322	13	Method of producing silicon
20	X		US 4356246 A	19821026	11	Method of making .alpha.-silicon powder, and electrophotographic materials incorporating said powder

	Current OR	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3
17	257/64	257/66; 257/E21.163 ; 257/E29.003 ; 257/E29.293 ; 257/E29.297 ; 257/E29.32; 257/E29.338 ; 257/E31.042 ; 257/E31.044 ; 257/E31.065 ; 430/84		Nakagawa; Katsumi et al.					
18	427/568	136/258; 257/E21.101 ; 427/561; 427/574; 427/585		Ishihara; Shunichi et al.					
19	423/349	204/164; 423/350; 427/452		Dahlberg; Reinhard					
20	430/136	204/192.26; 252/501.1; 427/578; 427/74; 430/58.25; 430/58.55; 430/84; 430/95; 430/96		Tabei; Masatoshi et al.					

	U	1	Document ID	Issue Date	Pages	Title
21	X		US 4332838 A	19820601	7	Particulate thin film fabrication process
22	X		US 20040175579 A	20040909	7	Passivating surface of substrate for use in corrosive and vacuum environments, by dehydrating surface, introducing and heating silicon hydride gas, depositing silicon layer, purging with inert gas, cycling substrate, and cooling substrate
23	X		US 20040175578 A	20040909	6	Passivating surface of substrate for use in corrosive and vacuum environments, by dehydrating surface, introducing and heating silicon hydride gas, depositing silicon layer, purging with inert gas, cycling substrate, and cooling substrate

	Current OR	Current XRef	Retrieval Classif	Inventor	S	C	P	2	3
21	427/74	117/43; 117/84; 117/933; 136/258; 427/248.1; 427/250; 427/251; 427/255.11; 427/255.25; 427/255.5; 438/482; 438/488; 438/509; 438/935		Wegrzyn; James E.					
22				BARONE, G A et al.					
23				BARONE, G A et al.					